Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

## 2SA1242

# Strobe Flash Applications Medium Power Amplifier Applications

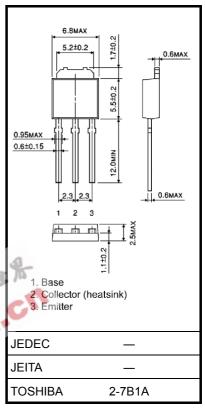
- Excellent hFE linearity
  - $h_{FE}(1) = 100 \text{ to } 320 \text{ (V}_{CE} = -2 \text{ V}, I_{C} = -0.5 \text{ A)}$
  - $: h_{FE}(2) = 70 \text{ (min) } (V_{CE} = -2 \text{ V}, I_{C} = -4 \text{ A})$
- Low collector saturation voltage
  - :  $V_{CE (sat)} = -1.0 \text{ V (max) (IC} = -4 \text{ A, IB} = -0.1 \text{ A)}$
- High power dissipation
  - :  $PC = 10 \text{ W (Tc} = 25^{\circ}\text{C}), PC = 1.0 \text{ W (Ta} = 25^{\circ}\text{C})$

#### Absolute Maximum Ratings (Ta = 25°C)

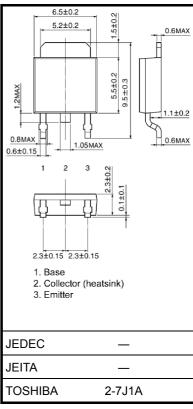
Characteristics		Symbol	Rating	Unit	
Collector-base voltage		$V_{CBO}$	-35	V	
Collector-emitter voltage		V <sub>CEO</sub>	-20	V	
Emitter-base voltage		V <sub>EBO</sub>	-8	V	
Collector current	DC	Ic	-5	CAO	
	Pulsed (Note 1)	ICP	-8		
Base current		IB	-0.5	Α	
Collector power dissipation	Ta = 25°C	PC	1.0	W	
	Tc = 25°C	FC	10		
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	−55 to 150	°C	

- Note 1: Pulse test: Pulse width = 10 ms (max), duty cycle = 30% (max)
- Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.36 g (typ.)



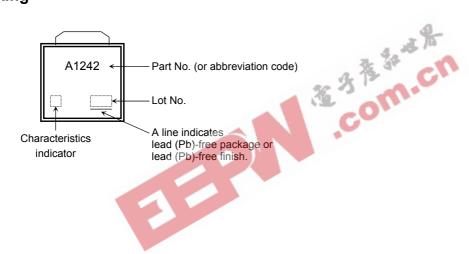
Weight: 0.36 g (typ.)

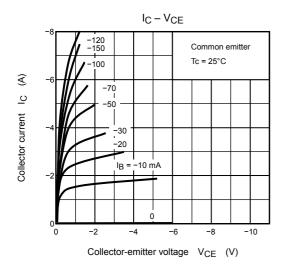
### **Electrical Characteristics (Ta = 25°C)**

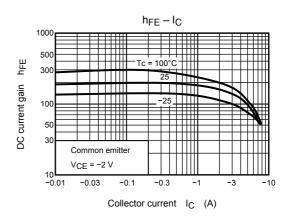
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = -35 \text{ V}, I_{E} = 0$	_	_	-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -8 V, I <sub>C</sub> = 0	_	_	-100	nA
Collector-emitter breakdown voltage	V <sub>CEO</sub>	$I_C = -10 \text{ mA}, I_B = 0$	-20	_	_	V
Emitter-base breakdown voltage	V <sub>EBO</sub>	$I_E = -1 \text{ mA}, I_C = 0$	-8	-	_	٧
DC current gain	h <sub>FE (1)</sub> (Note 3)	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A	100		320	
	h <sub>FE (2)</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -4 A	70	_	_	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = -4 A, I <sub>B</sub> = -0.1 A	_	_	-1.0	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -4 A	_	_	-1.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A	_	170	_	MHz
Collector output capacitance	C <sub>ob</sub>	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$	_	62	_	pF

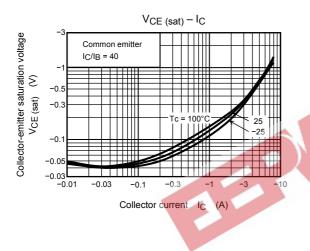
Note 3: h<sub>FE (1)</sub> classification O: 100 to 200, Y: 160 to 320

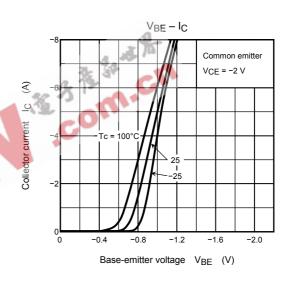
### Marking

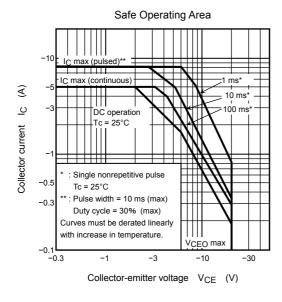


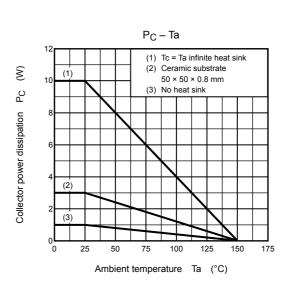












3

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